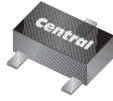


CMUDM8001

**SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**

ULTRAmini™



SOT-523 CASE



www.centra-semi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUDM8001 is an Enhancement-mode P-Channel Field Effect Transistor, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(on)}$ and Low Threshold Voltage.

MARKING CODE: C8A

FEATURES:

- Power Dissipation 250mW
- Low $r_{DS(on)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, SOT-523 Surface Mount Package
- Complementary Device: CMUDM7001

APPLICATIONS:

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Continuous Drain Current
Power Dissipation
Operating and Storage Junction Temperature

SYMBOL

V_{DS} 20
 V_{GS} 10
 I_D 100
 I_D 200
 P_D 250
 T_J, T_{stg} -65 to +150

UNITS

V
V
mA
mA
mW
 $^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSS}, I_{GSSR}	$V_{GS}=10\text{V}, V_{DS}=0$			1.0	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=100\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6		1.1	V
$r_{DS(ON)}$	$V_{GS}=4.0\text{V}, I_D=10\text{mA}$			8.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=10\text{mA}$			12	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=1.0\text{mA}$			45	Ω
g_{FS}	$V_{DS}=10\text{V}, I_D=100\text{mA}$	100			mS
C_{rss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
C_{iss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
C_{oss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
t_{on}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		35		ns
t_{off}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$		80		ns

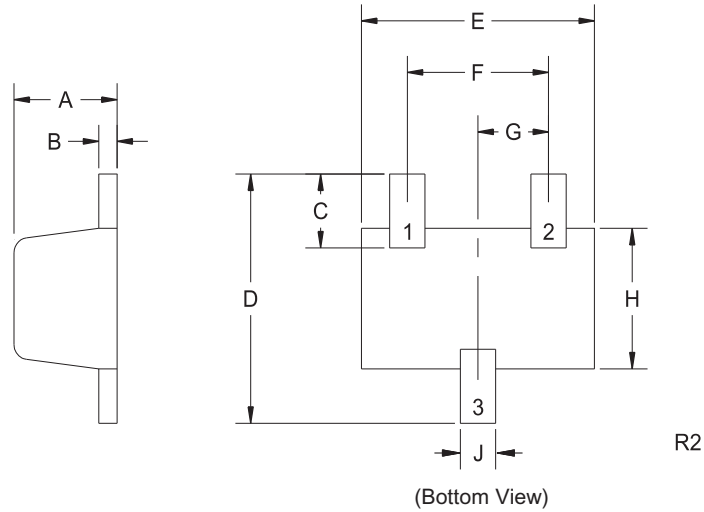
R1 (9-February 2010)

CMUDM8001

SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



SOT-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: C8A

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.023	0.031	0.58	0.78
B	0.002	0.008	0.04	0.20
C	0.013	0.021	0.34	0.54
D	0.059	0.067	1.50	1.70
E	0.059	0.067	1.50	1.70
F	0.035	0.043	0.90	1.10
G	0.020		0.50	
H	0.031	0.039	0.78	0.98
J	0.010	0.014	0.25	0.35

SOT-523 (REV: R2)

R1 (9-February 2010)

www.centalsemi.com

www.DataSheet4U.com

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